TOSHIBA Transistor Silicon NPN Epitaxial Type

# 2SC5692

High-Speed Switching Applications DC-DC Converter Applications Strobe Applications

- High DC current gain:  $h_{FE} = 400$  to 1000 ( $I_{C} = 0.3$  A)
- Low collector-emitter saturation voltage:  $V_{CE (sat)} = 0.14 \text{ V (max)}$
- High-speed switching:  $t_f = 120$  ns (typ.)

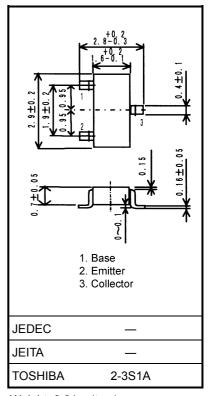
### Maximum Ratings (Ta = 25°C)

| Characteristics             |          | Symbol           | Rating     | Unit |  |
|-----------------------------|----------|------------------|------------|------|--|
| Collector-base voltage      |          | V <sub>CBO</sub> | 100        | V    |  |
| Collector-emitter voltage   |          | V <sub>CEX</sub> | 80         | V    |  |
| Collector-emitter voltage   |          | V <sub>CEO</sub> | 50         | V    |  |
| Emitter-base voltage        |          | V <sub>EBO</sub> | 7          | V    |  |
| Collector current           | DC       | IC               | 2.5        | Α    |  |
|                             | Pulse    | I <sub>CP</sub>  | 4.0        |      |  |
| Base current                |          | ΙΒ               | 250        | mA   |  |
| Collector power dissipation | DC       | PC               | 625        | mW   |  |
|                             | t = 10 s | (Note)           | 1000       |      |  |
| Junction temperature        |          | Tj               | 150        | °C   |  |
| Storage temperature range   |          | T <sub>stg</sub> | -55 to 150 | °C   |  |

Note: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

#### **Industrial Applications**

Unit: mm

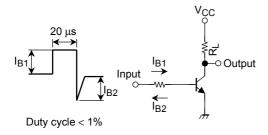


Weight: 0.01 g (typ.)

## **Electrical Characteristics (Ta = 25°C)**

| Characteristics                      |              | Symbol                | Test Condition  | Min | Тур. | Max  | Unit |
|--------------------------------------|--------------|-----------------------|---|-----|------|------|------|
| Collector cut-off current            |              | I <sub>CBO</sub>      | V <sub>CB</sub> = 100 V, I <sub>E</sub> = 0           | _   | _    | 100  | nA   |
| Emitter cut-off current              |              | I <sub>EBO</sub>      | $V_{EB} = 7 \text{ V, } I_{C} = 0$                    | _   | _    | 100  | nA   |
| Collector-emitter breakdown voltage  |              | V (BR) CEO            | I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0            | 50  | _    | _    | V    |
| DC current gain                      |              | h <sub>FE</sub> (1)   | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.3 A         | 400 | _    | 1000 |      |
|                                      |              | h <sub>FE</sub> (2)   | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 1 A           | 200 | _    | _    |      |
| Collector-emitter saturation voltage |              | V <sub>CE (sat)</sub> | I <sub>C</sub> = 1 A, I <sub>B</sub> = 20 mA          | _   | _    | 0.14 | V    |
| Base-emitter saturation voltage      |              | V <sub>BE (sat)</sub> | I <sub>C</sub> = 1 A, I <sub>B</sub> = 20 mA          | _   | _    | 1.10 | V    |
| Collector output capacitance         |              | C <sub>ob</sub>       | V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz | _   | 13   | _    | pF   |
| Switching time                       | Rise time    | t <sub>r</sub>        | See Figure 1 circuit diagram.                         | _   | 40   | _    |      |
|                                      | Storage time | t <sub>stg</sub>      | $V_{CC} \simeq 30 \text{ V}, R_L = 30 \Omega$         | _   | 500  | _    | ns   |
|                                      | Fall time    | t <sub>f</sub>        | $I_{B1} = -I_{B2} = 33.3 \text{ mA}$                  | _   | 120  | _    |      |

# Marking



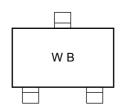
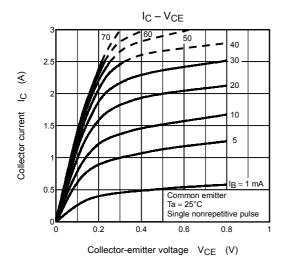
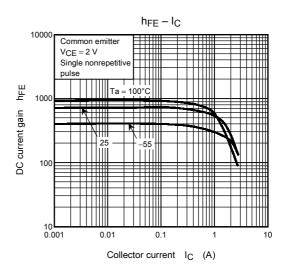
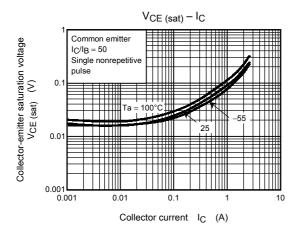
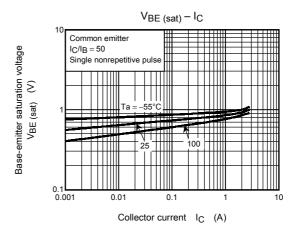


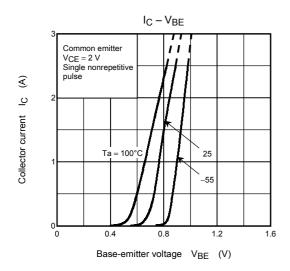
Figure 1 Switching Time Test Circuit & Timing Chart

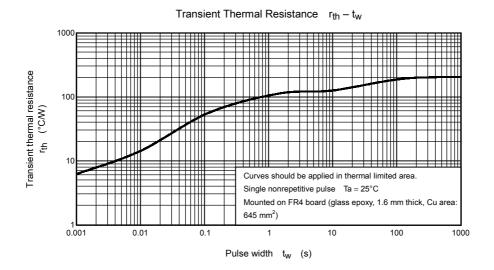


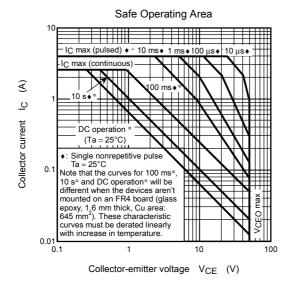












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